

#### 40V +175°C N-CHANNEL ENHANCEMENT MODE MOSFET PowerDI5060-8

## **Product Summary**

BV <sub>DSS</sub>	R <sub>DS(ON)</sub> max	I <sub>D</sub> T <sub>C</sub> = +25°C (Note 10)
40V	$1.8 \text{m}\Omega$ @ $V_{GS} = 10V$	100A

#### **Features**

- Rated to +175°C Ideal for High Ambient Temperature Environments
- 100% Unclamped Inductive Switching (UIS) Test in Production Ensures More Reliable and Robust End Application
- Thermally Efficient Package-Cooler Running Applications
- High Conversion Efficiency
- Low R<sub>DS(ON)</sub> Minimizes On State Losses
- <1.1mm Package Profile Ideal for Thin Applications
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

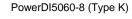
## **Description and Applications**

This MOSFET is designed to meet the stringent requirements of Automotive applications. It is qualified to AEC-Q101, supported by a PPAP and is ideal for use in:

- Engine Management Systems
- Body Control Electronics
- DC-DC Converters

#### **Mechanical Data**

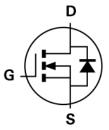
- Case: PowerDI<sup>®</sup>5060-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Finish Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 @3
- Weight: 0.097 grams (Approximate)



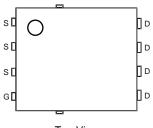




Top View Bottom View







Top View Pin Configuration

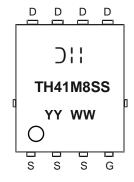
## Ordering Information (Note 5)

Part Number	Case	Packaging
DMTH41M8SPSQ-13	PowerDI5060-8 (Type K)	2,500 / Tape & Reel

Notes:

- 1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds
- <1000ppm antimony compounds.</p>
  4. Automotive products are AEC-Q101 qualified and are PPAP capable. Refer to https://www.diodes.com/quality/.
- 5. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/

# **Marking Information**



☐ H = Manufacturer's Marking TH41M8SS = Product Type Marking Code YYWW = Date Code Marking YY = Last Two Digits of Year (ex: 19 = 2019) WW = Week Code (01 to 53)

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# **Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Drain-Source Voltage	$V_{DSS}$	40	V	
Gate-Source Voltage	$V_{GSS}$	±20	V	
Continuous Drain Current, V <sub>GS</sub> = 10V (Notes 7 & 10)	$T_{C} = +25^{\circ}C$ $T_{C} = +100^{\circ}C$	I <sub>D</sub>	100 100	А
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)	I <sub>DM</sub>	400	Α	
Pulsed Body Diode Forward Current (10µs Pulse, Duty Cycle = 1%)	I <sub>SM</sub>	400	Α	
Continuous Body Diode Forward Current (Note 7) T <sub>C</sub> = +25°C		Is	100	Α
Avalanche Current, L = 0.1mH	I <sub>AS</sub>	72.8	Α	
Avalanche Energy, L = 0.1mH	E <sub>AS</sub>	265	mJ	

# **Thermal Characteristics**

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 6)	P <sub>D</sub>	3.03	W
Thermal Resistance, Junction to Ambient (Note 6)	$R_{ heta JA}$	49	°C/W
Total Power Dissipation (Note 7)	P <sub>D</sub>	150	W
Thermal Resistance, Junction to Case (Note 7)	$R_{ heta JC}$	1.0	°C/W
Operating and Storage Temperature Range	T <sub>J,</sub> T <sub>STG</sub>	-55 to +175	°C

# **Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 8)							
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	40	1	1	V	$V_{GS} = 0V, I_D = 250\mu A$	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	1	_	1	μA	$V_{DS} = 32V, V_{GS} = 0V$	
Gate-Source Leakage	I <sub>GSS</sub>		_	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 8)							
Gate Threshold Voltage	$V_{GS(TH)}$	2		4	V	$V_{DS} = V_{GS}$ , $I_D = 250\mu A$	
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	l	1.4	1.8	mΩ	$V_{GS} = 10V, I_D = 30A$	
Diode Forward Voltage	$V_{SD}$		0.8	1.2	V	$V_{GS} = 0V, I_{S} = 20A$	
DYNAMIC CHARACTERISTICS (Note 9)							
Input Capacitance	C <sub>iss</sub>	1	6968	_	pF	$V_{DS} = 20V$ , $V_{GS} = 0V$ , $f = 1MHz$	
Output Capacitance	Coss	l	1812	1			
Reverse Transfer Capacitance	C <sub>rss</sub>		59	-			
Gate Resistance	R <sub>G</sub>	1	1.21	_	Ω	$V_{DS} = 0V$ , $V_{GS} = 0V$ , $f = 1MHz$	
Total Gate Charge	$Q_g$	l	79.5	1		$V_{DD} = 20V, I_D = 90A,$	
Gate-Source Charge	$Q_{gs}$		20.6		nC		
Gate-Drain Charge	$Q_{gd}$	_	16.5	_		$V_{GS} = 10V$	
Turn-On Delay Time	t <sub>D(ON)</sub>	_	13.3	_		$V_{DD} = 20V, V_{GS} = 10V,$ $I_{D} = 90A, R_{G} = 3.5\Omega$	
Turn-On Rise Time	t <sub>R</sub>		41.3		ns		
Turn-Off Delay Time	t <sub>D(OFF)</sub>	_	35.1	_			
Turn-Off Fall Time	t <sub>F</sub>	_	13.7	_			
Reverse Recovery Time	t <sub>RR</sub>	_	62	_	ns		
Reverse Recovery Charge	Q <sub>RR</sub>	_	103	_	nC		

Notes:

- 6. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.
  7. Thermal resistance from junction to soldering point (on the exposed drain pad).
  8. Short duration pulse test used to minimize self-heating effect.
  9. Guaranteed by design. Not subject to product testing.
  10. Limited by package.





50.0

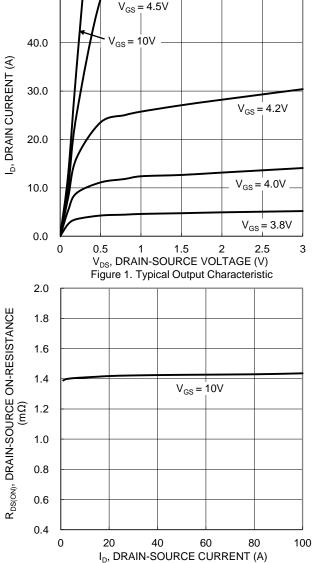


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

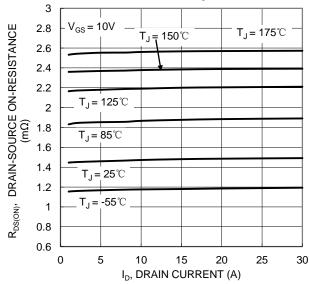
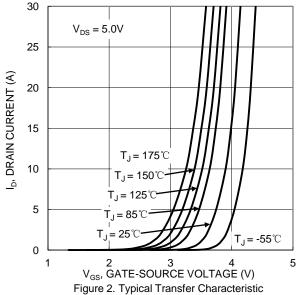
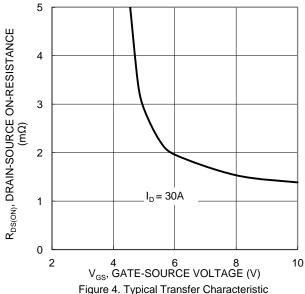


Figure 5. Typical On-Resistance vs. Drain Current and Temperature





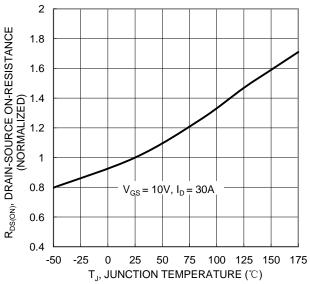


Figure 6. On-Resistance Variation with Temperature





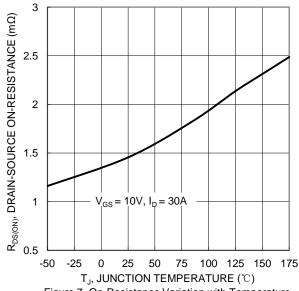


Figure 7. On-Resistance Variation with Temperature

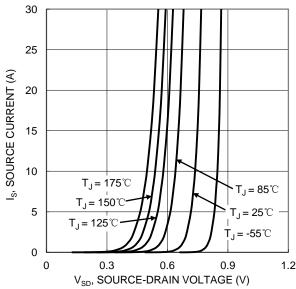
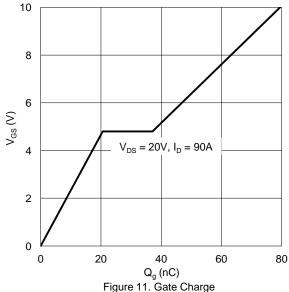
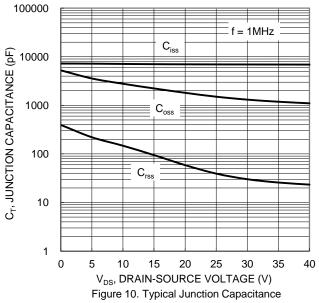


Figure 9. Diode Forward Voltage vs. Current



4 3.5  $V_{GS(TH)},$  GATE THRESHOLD VOLTAGE (V) 3  $I_D = 1 \text{mA}$ 2.5 2  $I_{D} = 250 \mu A$ 1.5 1 0.5 0 75 100 125 150 175 -50 -25 0 25 50 T<sub>J</sub>, JUNCTION TEMPERATURE (°C)

Figure 8. Gate Threshold Variation vs. Junction Temperature



1000  $\begin{array}{c} R_{DS(ON)} \\ Limited \end{array}$ 100 ID, DRAIN CURRENT (A)  $P_W = 10\mu s$ 10 T<sub>J(Max)</sub> = 175℃  $T_C = 25^{\circ}C$ Single Pulse 1 = 100ms DUT on Infinite Heatsink  $V_{GS} = 10V$ 0.1 0.1 10 100  $V_{DS}$ , DRAIN-SOURCE VOLTAGE (V)

Figure 12. SOA, Safe Operation Area



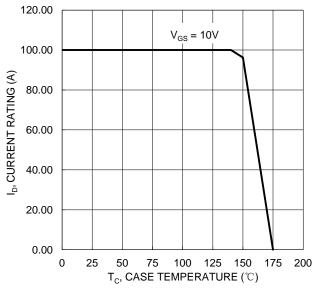


Figure 13. Current De-rating

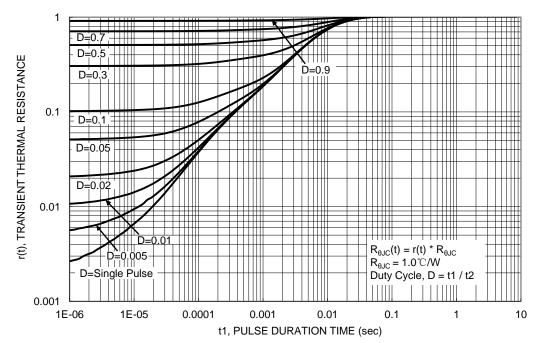


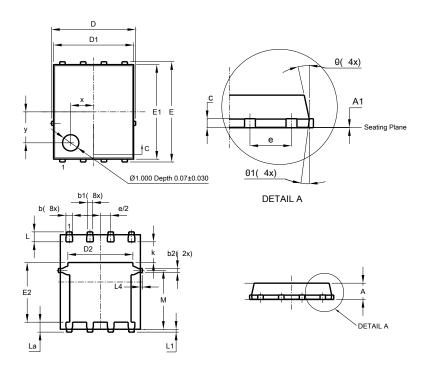
Figure 14. Transient Thermal Resistance



# **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### PowerDI5060-8 (Type K)

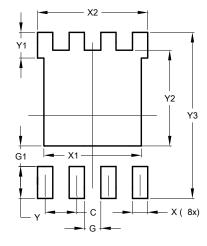


PowerDI5060-8 (Type K)				
Dim	Min	Max	Тур	
Α	0.90	1.10	1.00	
A1	0	0.05	0.02	
b	0.33	0.51	0.41	
b1	0.300	0.366	0.333	
b2	0.20	0.35	0.25	
С	0.23	0.33	0.277	
D	5	.15 BS0		
D1	4.85	4.95	4.90	
D2	-	-	3.98	
Е	6	.15 BS0		
E1	5.75	5.85	5.80	
E2	3.56	3.725	3.66	
е	1	.27BSC		
k	-	-	1.27	
L	0.51	0.71	0.61	
La	0.51	0.675	0.61	
L1	0.05	0.20	0.175	
L4	-	-	0.125	
М	3.50 3.71		3.605	
Х	-	-	1.400	
у	-	-	1.900	
θ	10°	12°	11°	
θ1	6°	8°	7°	
All Dimensions in mm				

# **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.

### PowerDI5060-8 (Type K)



Dimensions	Value (in mm)		
С	1.270		
G	0.660		
G1	0.820		
X	0.610		
X1	3.910		
X2	4.420		
Y	1.270		
Y1	1.020		
Y2	3.810		
Y3	6.610		

March 2019

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